

**SURFACE MOUNT
SCHOTTKY BARRIER RECTIFIERS**

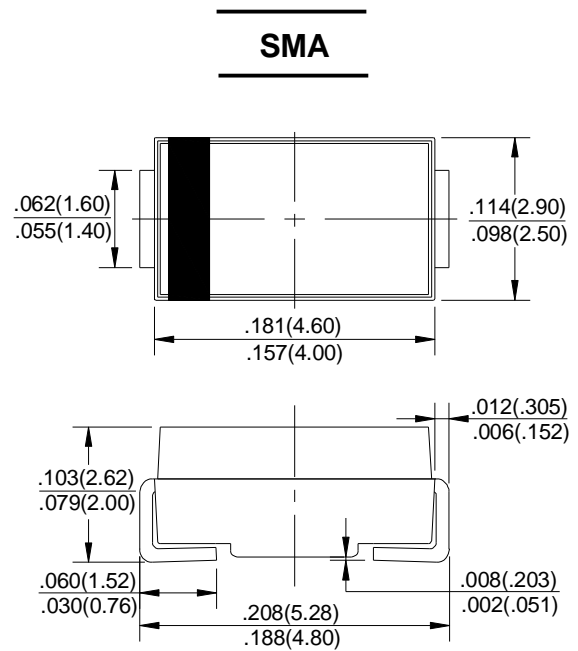
REVERSE VOLTAGE - **20 to 40** Volts
FORWARD CURRENT - **1.0** Amperes

FEATURES

- Metal-Semiconductor junction with guard ring
- Epitaxial construction
- Low forward voltage drop
- High current capability
- The plastic material carries UL recognition 94V-0
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- Case: Molded Plastic
- Polarity: Indicated by cathode band
- Weight: 0.002 ounces, 0.064 grams



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave ,60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	SM5817	SM5818	SM5819	UNIT
Maximum Recurrent Peak Reverse Voltage	VRRM	20	30	40	V
Maximum RMS Voltage	VRMS	14	21	28	V
Maximum DC Blocking Voltage	VDC	20	30	40	V
Maximum Average Forward Rectified Current @TA =75 °C	I(AV)	1.0			A
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed on Rated Load(JEDEC Method)	IFSM	40			A
Maximum Forward Voltage at 1.0A DC	VF	0.450	0.550	0.600	V
Maximum Forward Voltage at 3.0A DC	VF	0.750	0.875	0.900	V
Maximum DC Reverse Current @TJ=25°C at Rated DC Blocking Voltage @TJ=100°C	IR	1.0			mA
		10			
Typical Junction Capacitance (Note1)	CJ	110			pF
Typical Thermal Resistance (Note2)	RθJA	80			°C/W
Operating Temperature Range	TJ	-55 to +150			°C
Storage Temperature Range	TSTG	-55 to +150			°C

NOTES: 1.Measured at 1.0 MHz and applied reverse voltage of 4.0V DC

2.Thermal resistance junction to ambient,

FIG. 1 - FORWARD CURRENT DERATING CURVE

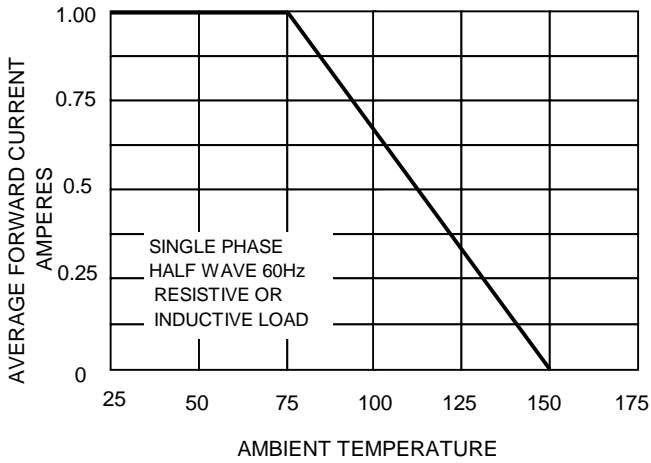


FIG. 2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

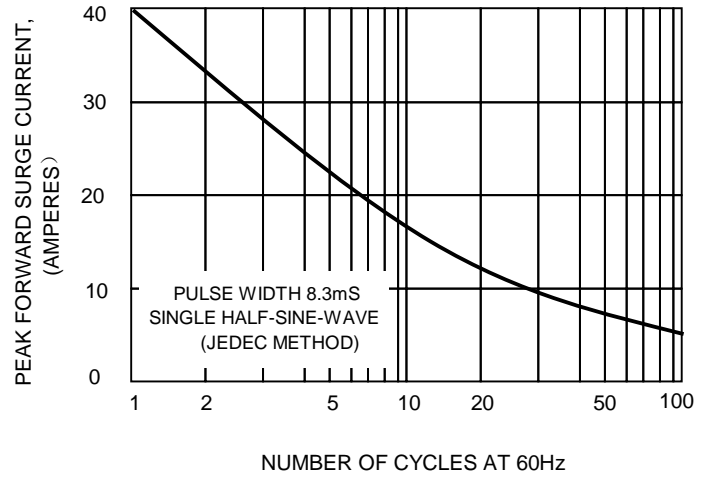


FIG.3 - TYPICAL JUNCTION CAPACITANCE

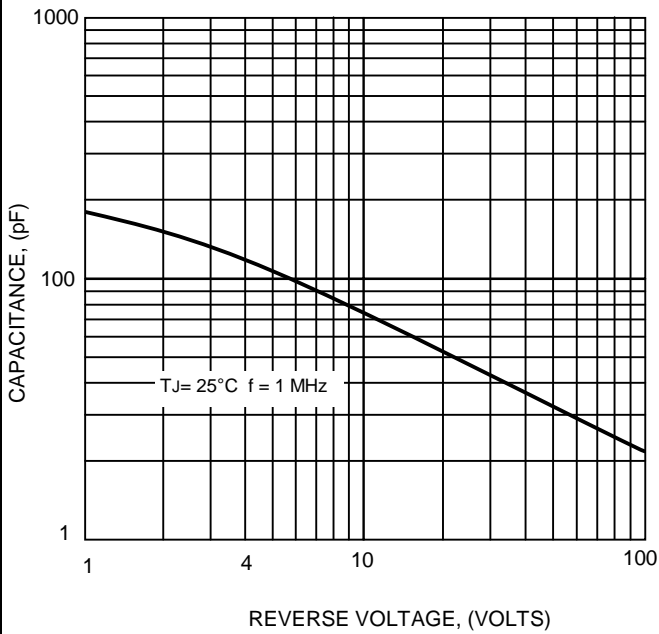


FIG.4-TYPICAL FORWARD CHARACTERISTICS

